

# מערכת eLINE – מדריך מקוצר למשתמש

# eLINE System – a brief operation guide





# **General Information**

#### **General system description:**

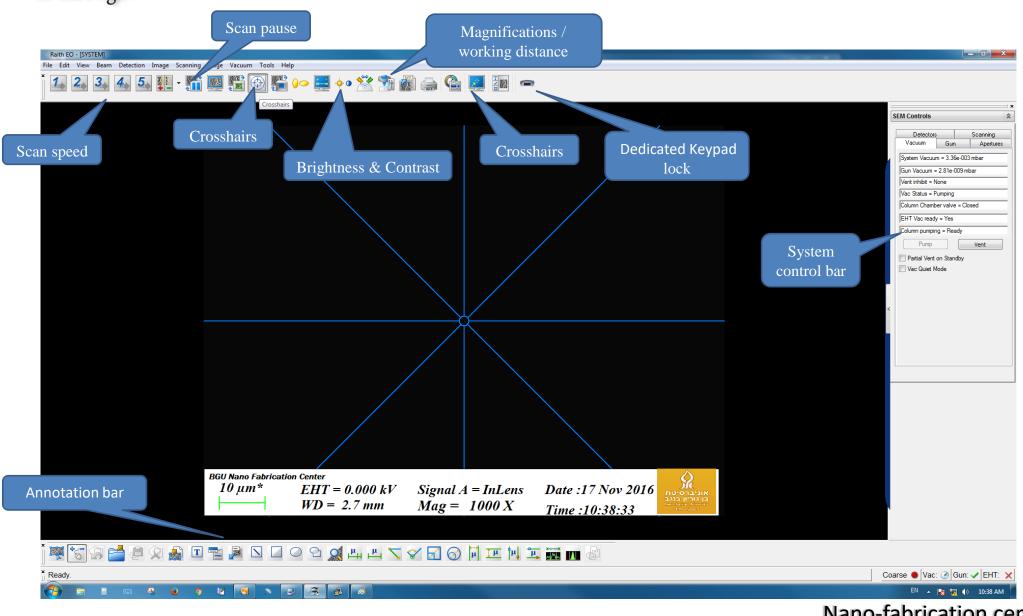
#### **Specifications:**

- □ Raith Company
- Leo Gemini Coulomb
- □ Stage position laser interferometer
- □ Stage height laser interferometer
- Stationary stage movement
- □ Gaussian beam shape profile
- Vector scan elements

- Encoder resolution 2nm
- □ Position repeatability « 50nm
- Dwell time 100nm-8s
- □ Step size 1nm-1mm
- □ High tension 0.1 kV to 30kV
- □ Setting time 0-10ms
- □ Write field 1nm-2mm
- □ Beam Current 1pA-10nA
- □ WD 2mm-15mm
- □ Spot resolution 20nm



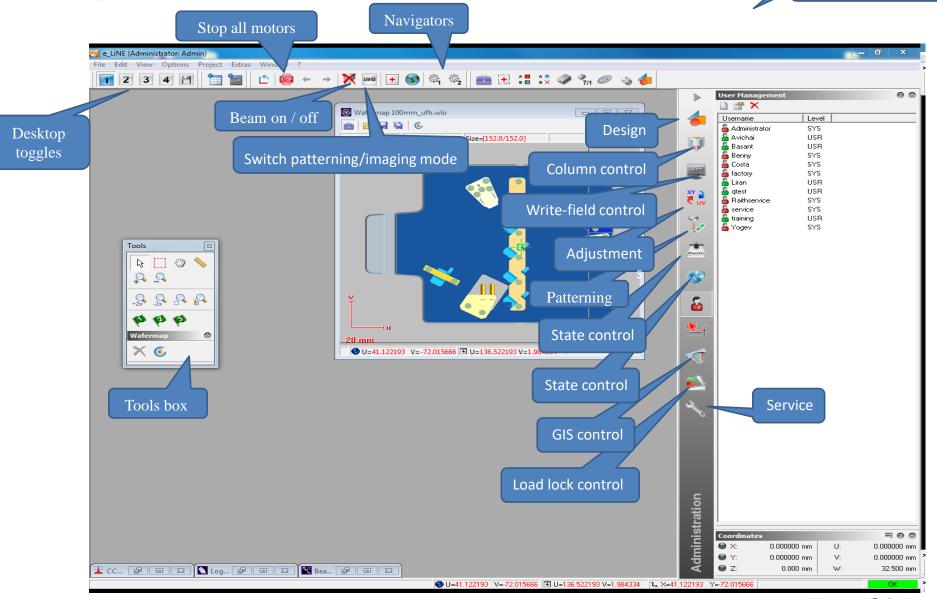
#### SEM software (right screen)





#### Raith eLINE software (left screen)

Magnifications / working distance



Nano-fabrication center



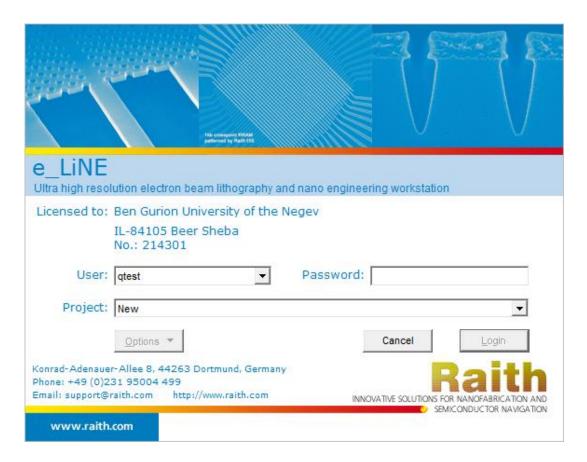
fundamental steps to successful e-beam lithography:

- 1. Loading sample
- 2. <u>Set desired EHT, aperture and pattern</u>
- 3. <u>Measure current and set suitable dose</u>
- 4. <u>Adjust axes</u>
- 5. <u>Focus</u>
- 6. Write-field alignment
- 7. Exposure
- 8. Unloading sample and developing



Enter your user name and password,

choose the project type and click "Login"

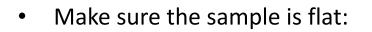


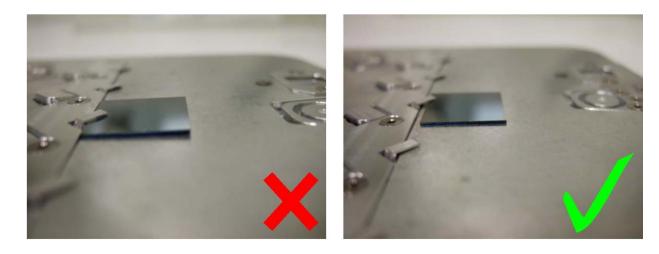


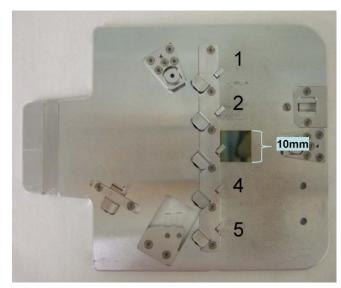
#### Loading sample

Placing the sample on holder:

- Select the suitable holder
- Take a note of the sample size and position on holder:
- It is recommended that the sample's bottom left corner is bare





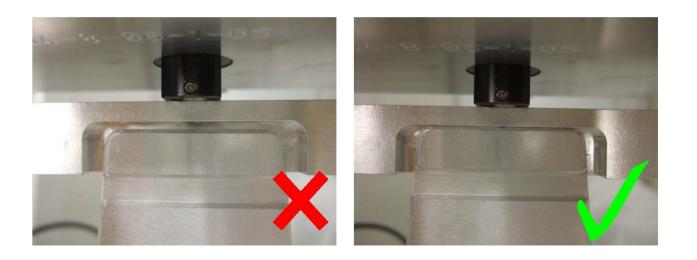


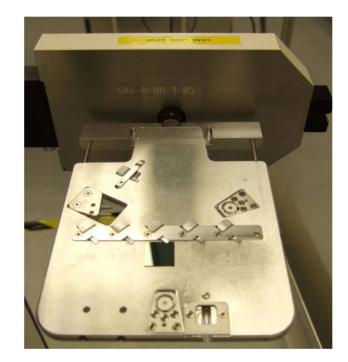


#### Loading sample

Place holder on transfer rod:

- Make sure it is leveled properly
- Make sure it is anchored correctly
- Close and fasten load-lock door







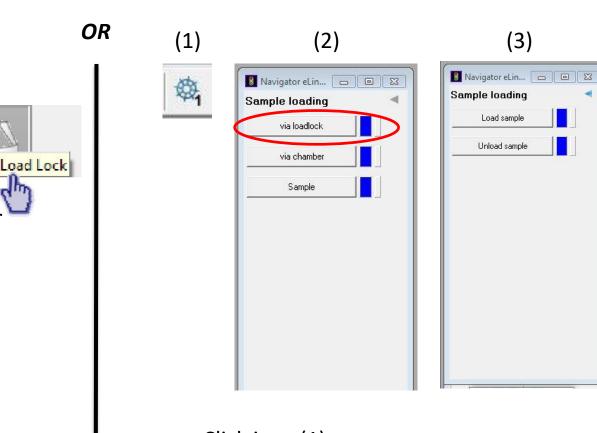
Raith eLINE software:

- Click on **Load-lock** sample ۲ exchange menu icon
- Click on Load sample on • "Sample exchange via load lock" bar

Sample	exchange			00	
	Sample excha	nge via l	oad lock		
$\triangleleft$	Load sample		Unload sample	e	V
	Sample excha	nge via fi	ront door		
	Load sample		Unload Sampl	e	Ś
	Pump chamber		Vent chambe	r	<b>e</b>
	Sample		Advanced		
Sample	name:				

#### Notice!

Using the "Sample exchange Via front door" menu will open The main chamber and lose the system vacuum!



- Click icon (1) ٠
- Choose via loadlock (2) ٠
- Choose "Load sample" (3) ٠

Nano-fabrication center

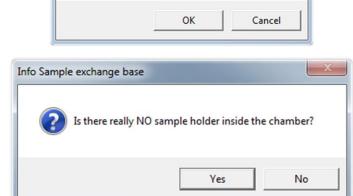
(3)

# Loading sample



• Click OK to proceed

 Insure that there is no sample holder inside the chamber and the holder is in place and click "Yes"



This procedure needs approx. 8 minutes.

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Loading sample

Press OK to proceed

Info Sample exchange

?

• Close and fasten the load lock door

- Click OK to proceed
- Wait until next info pop-up window appears



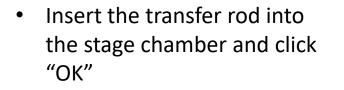


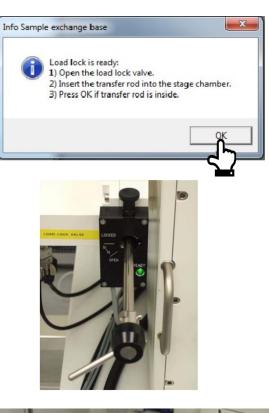


### Loading sample

 When this pop-up appears, insure that the load lock vacuum ready indicator is on

• Open the load lock valve









• When this pop-up appears, remove the transfer rod from the stage chamber

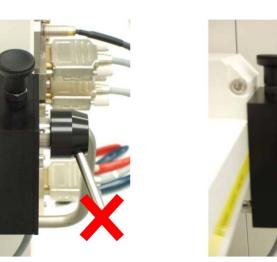
 Close the valve. Make sure that it is placed in "Locked" position

#### Loading sample





• Click OK to proceed



6

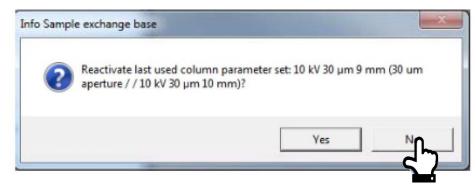


#### Loading sample

Reset coordinate system? Click as required



Reactive last used column parameter? Click as required



Load procedure finished successfully ? Click on "OK"

Name the sample

Sample Information		×
Please specify sample name.		
	Cancel	ОК





#### Set desired EHT, aperture and pattern

 Click on "Column control" icon

- Select the desired mode
- Er () 10 um aperture / O 10 kV 10 μm 10 mm O 20 kV 10 μm 10 mm · 🔘 30 kV 10 μm 10 mm 🔘 30 um aperture / 10kV 30 µm 10mm O 20 kV 30 μm 10 mm 🔿 30 kV 30 μm 10 mm O 60 um aperture / O 10 kV 60 μm 10 mm 🔘 20 kV 60 μm 10 mm · 🔘 30 kV 60 μm 10 mm 👯 System Ramp-down Modes Ė... O Column Standby 🕑 Column Stop Column Control 00 🔲 🗟 🗋 🗹 🗙 🗔 5 ۲

Active Mode: Stop (GUN Settings)

E O 10 um aperture /

 Click on "Activate selected mode" icon





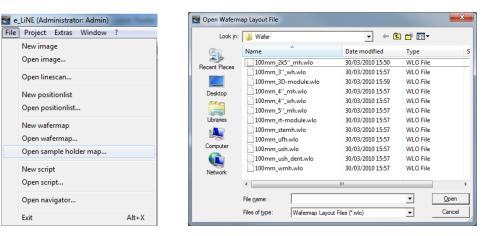
#### Set desired EHT, aperture and pattern

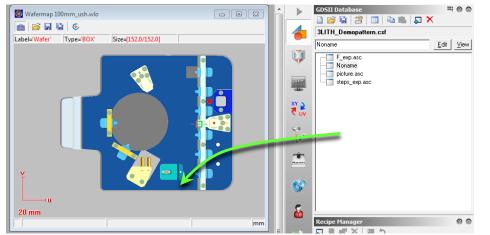
Click on "Design" icon



- Open GDSII database file
- Open the required sample holder map layout

 Choose the desired structure and drag it to the sample position on the wafer-map. A new position list window should appear with the structure position parameters





_	itionlist N			X		🖬 👻 🕨 🔤 Include:	all	▼ Exclude: none ▼			
ID		-		Template	-	Options		Туре	Pos1/um	Pos2/um	Pos3/um
0	14.43935	0.296184	XN	UV	s1000w			EXPOSURE	50.000	50.000	
			1	1							



#### **Current measurements and suitable dose set**

- Move the stage to be in a working distance of 10mm (use command line 25.5z or drive to W=10mm or to Z=~25.5mm)
- Move to the faraday cup position
- Make sure that your on the faraday cup position
- Re-measure the beam current to ensure its stability
- Ensure that the measured current is suite to the official current table

Stage Control	0 0
STOP @ mm @	lase • UV C XY
Drive     Step     Positions     Stage L       U:	Position or absolute
Comman 25.5z	d line Repeat
Image: mail of μm     Image: mail of μm	ase ● UV ○ XY
Drive Step Positions Stage L free Faraday Cup on holder Exchange position Load position Point 1 Point 2 free free free	<u><u>G</u>o</u>
Beam Current	
0.1456 nA notmeasured Apeture: 30.0 µm Votage: 10.00 kV	🕅 drive back
(current position)	Measure



#### **Current measurements and suitable dose set**

**Patterning Parameter** 

Size

Area Step Size:

Area Line Spacing:

Area Dwell Time:

Line Step Size:

Line Dwell Time:

Curved elements

Curve Line Spacing: 0.0020 µm

Curve Dwell Time: 0.001000 ms

Curve Step Size:

✓ Lines

100.0000 μm

0.0200 µm

0.0020 µm

0.0100 µm

0.0200 µm

🔽 Equal steps

0.000750 ms

Equal steps
0.001000 ms

0 0

=> 10 Pixel

=> 1 Pixel

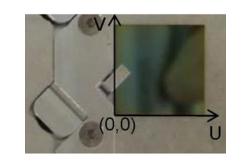
- In the patterning parameter menu, mark the needed types of elements (Lines, Curved elements, Dots, etc.)
- Click on the patterning parameter calculator icon
- Set the Step size and Dose for each type of elements
- Calculate the **Dwell time** for each type of elements
- Note that the calculated beam speed should not exceed 15mm/s (otherwise change the parameters or even the EHT and aperture in order to have different beam current)
- Note that the headers and notification area is NOT red

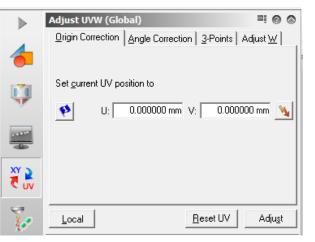
	Patterning Parameter Calculation				Det Duvell Time: 0.250000 me
X	Write Field Size: 100.0000 μm Min. Step Size: 0.0020 μm Beam <u>C</u> urrent: 0.100000 nA	≜treas     Qurved Elements     Lines     Qots       Area Step Size:     0.0200 µm     III       Area Line Spacing:     0.0200 µm     III       Area Davel Line:     0.001000 ms     III       Area Davel Line:     100.000000 µC/cm²     III       Beam Speed     20.000000 mm/s     III	Equal steps Patterning Parameter Calculation	X	Dot Dwell Time: 0.250000 ms FBMS / MBMS elements only FBMS Areas FBMS Lines
	Area Dose = (Beam Current * Area Dwell Tim		Write Field Size: 100.0000 µm	Areas <u>C</u> urved Elements Lines <u>D</u> ots Area <u>S</u> tep Size: 0.0080 μm	MBMS Elements
	L	V	Min. Step Size: 0.0020 μm Beam <u>C</u> urrent: 0.100000 nA	Area Line Spacing:   0.0080 μm   Image: Equal steps     Area Dwell Lime:   0.000640 ms     Area Dose:   100.00000 μC/cm     Beam Speed:   12.5000000 mm/s	
			Area Dose = (Beam Current * Area Dwell Time	e) / (Step Size"Line Spacing) Cancel OK	Nano-fabrication center



#### **Adjust axes**

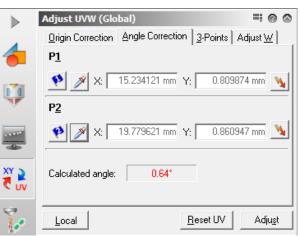
 Adjust the origin correction by It is recommended to set the down left corner of the sample to U:0,V:0.





- If necessary, Adjust the angle correction by using two points on the x axis of the sample/wafer, read there XY positions (P1, P2) and click "Adjust". The calculated angle will appear
- If necessary, also perform the 3point alignment procedure

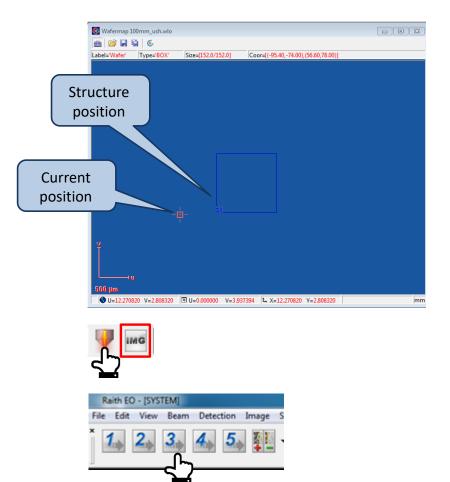






- Move close to the exposure coordinates of the structure placed on the wafer-map
- Turn the beam on and ensure that the system is in imaging mode
- Reduce the scanning window, increase the magnification and decrease the scan speed
- Focus on the sample surface for optimum image

### Focus

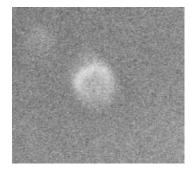




# Focus

- While the beam turned on, left click on "Burn a spot" icon. Fine tune the focusing until getting a clear and small point (~20nm diameter)
- Adjust the stigmator's XY nodes until the circle is ideal
- Adjust brightness and contrast as needed
- Repeat the spot burning to ensure the focus is ideal
- Ensure that the working distance (WD) from the sample is reasonable (9-10mm)
- Ensure that the spot is clearly visible and the croshairs mark centered to this spot







#### Write-field alignment

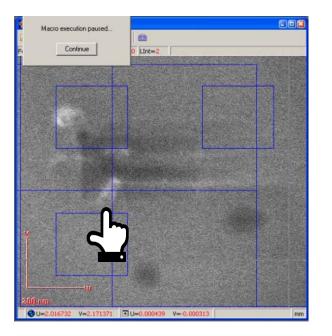
- Click on the "Writefield control" icon
- At the "Writefield manager" tab select the proper writefield and click "F9" or "Set new writefield" icon.
- In the "Scan manager" tab, select the needed alignment procedure, accordingly to the writefield size selected and click "F9" or right click and select "Execute". For example at the "Manual" sub header select "100um WF manual 25um marks" and click execute.
- Usually start with the largest scan size to the smallest one.

	Writefield Manager	👩 🔽 Databa	O (		
1	Magnification		130 Values		
6	Magnification x 1000		.000 μm		
1	Name	Mag. +	Size/µm		
V	100 x, 1000.0 µm	100	1000.000		
	500 x, 200.0 µm	500	200.000		
a 41 <sup>0</sup>	🧭 1000 x, 100.0 μm	1000	100.000		
	2000 x, 50.0 µm	2000	50.000		
	4000 x, 25.0 µm	4000	25.000		
Vritefie	eld Control <sup>0</sup> x, 1.0 µm	100000	1.000		
e l					
•					
	9	ican Manag	jer	≕ 0	6
******	a a a a a a a a a a a a a a a a a a a	🕈   🗈 🗋	) 🖉 🗙	<u>A</u>	
	· [	: + • 🗲 Linesa	cans		
	F	- 📰 Writef	ield Alianmer	nt Procedures	
			utomatic with		
				-	
			utomatic with		
		🕂 🕀 🔁 🕀	DSII Layer B	ased Mark Scans	
		📥 🗠 🛄 M	anual		
		· 🖬	100 um Wi	F - Manual ALWF 1 um marks	
			-	F - Manual ALWF 25 um marks	E
				F - Manual ALWF 5 um marks	
		🖬	🚦 1000 um V	/F - Manual ALWF 10 um marks	
		🗈	] 1000 um V	VF - Manual ALWF 100 um marks	
		🖬	1000 um V	/F - Manual ALWF 50 um marks	
		🖬	25 um WF	- Manual ALWF 1 um marks	
				- Manual ALWF 5 um marks	1.4



#### Write-field alignment

- Executing a WF procedure would start a macro that will scan the field from several marks so it can be fine aligned.
- Use a the centered spot as the center reference point and drag the cursor to this point by (Ctrl+Left click) and click "Continue"
- After the macro will finish, execute another procedure with smaller scan field size until reaching to the smallest scan size for higher resolution
- The Zoom, Shift and rotation parameters will appear after each iteration. Accept them if they seem reasonable. Check the reasonability of the final values of the parameters at the Writefield alignment tab.
- Run the procedure as needed until the cursor change is negligible



Writefield	Alignment		≕ 0 ⊘
Zoom	U: 0.92000	1.00000	<u>G</u> et marks
beam 💌	V: 0.92000	1.00000	Marks: 0 💌
Shift	U: 0.000 µm	0.000 µm	
beam 💌	V: 0.000 μm	0.000 µm	
Rotation	U: 0.000 deg	0.000 deg	<u>R</u> eset
beam 💌	V: 0.000 deg	0.000 deg	<u>S</u> end



#### Verify that the final exposing parameters are ٠ correct:

1. Exposing parameters are set correctly

Exposure

Positionlist NONAME.pls

● 1 11.99287: -0.426485XN

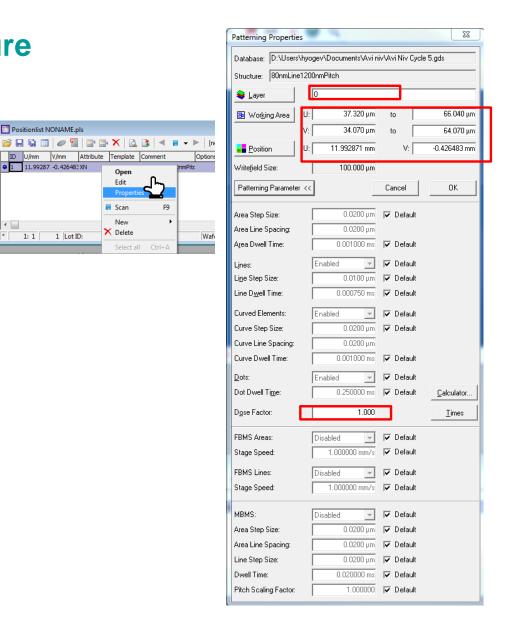
•

1:1

1 Lot ID:

In the patterning properties pop-up window (right click on the structure line and click "**Properties**"):

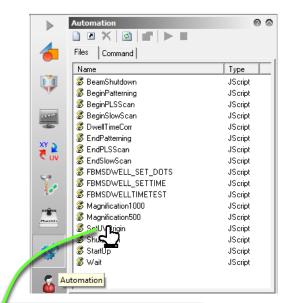
- Structure position is correct 1.
- 2. Selected layers are correct
- Working area is correct 3.
- 4. Dose factor is as needed





#### Exposure

- In the "Automation" tab, drag the needed macro to the position list to run it during or after the scan exposure process.
- For shutting down the beam (close EHT) after scan exposure is finished , drag the BeamShutDown macro to the end of the position list.



🐞 Pos	sitionlist N	ONAME.pl	s							
12 E	1 🖬 💷	Ø 🖥		×   🖾	😫 < 🖬 🕶 I	Include: all	Exclude: none	·		
ID	U/mm	V/mm	Attribute	Template	Comment	Options	T	Pos1/um	Pos2/um	Pos3/um l
• 1	11.99287	-0.426483	XN	UV	80nmLine 1200nmPite		EXPOSURE	50.000	50.000	
2	0.000000	0.000000 1	MN	dUV		STAY	MACRO			
•										•
										F
*	1:1	1 Lot ID	l:			WaferID:		Slot:		



Raith eLINE software:

• Click on Load-lock sample exchange menu icon



• Click on Unload sample on "Sample exchange via load lock" bar

Sample	exchange		6	
	Sample exch	ange via lo	oad lock	
\$	Load sample	$\searrow$	Unload sample	
	Sample excha	ange via fr	ront door	
	Load sample		Unload Sample	
	Pump chamber		Vent chamber	
	Sample		Advanced	
Sample	name:			

Notice!

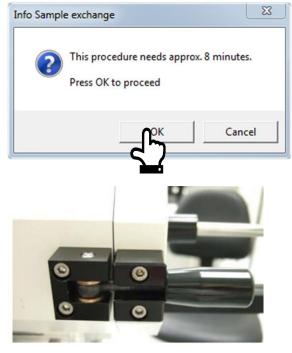
Using the "Sample exchange Via front door" menu will open The main chamber and lose the system vacuum!



• Click OK to proceed

Close and fasten the load lock door



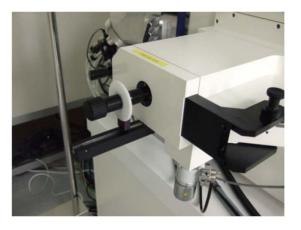


• Click OK to proceed









 When the load lock vacuum is ready, open the load lock valve, insert the rod and click OK



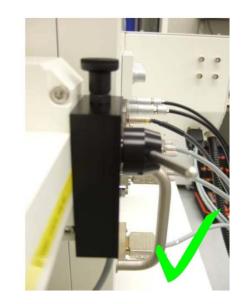


- After the holder is placed in the exchange place the "Info sample exchange base" pop-up window will appear
- Remove the transfer rod, close the load lock valve and click **OK**











- Click OK when the unload procedure finished completely. Wait for 1-2 minutes until the load lock chamber is vented, and the venting has stopped.
- Unload the holder and remove the sample.
- Close the load lock door and fasten it gently.
- Place the holder in its dedicated box in the eLINE room bookcase drawer.

